August 2014

FDPF33N25T

N-Channel UniFET^{TM} MOSFET

250 V, 33 A, 94 mΩ

Features

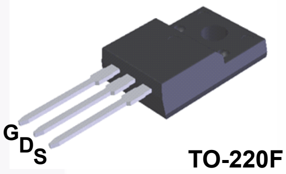
- $R_{DS(on)}$ = 94 mΩ (Max.) @ V_{GS} = 10 V, I_D = 16.5 A
- Low Gate Charge (Typ. 36.8 nC)
- Low C_{rss} (Typ. 39 pF)
- 100% Avalanche Tested

Applications

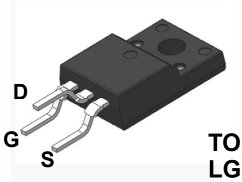
- PDP TV
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

Description

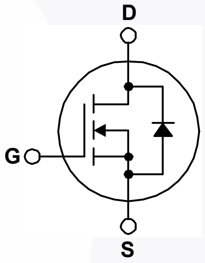
UniFET^{TM} MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



TO-220F



TO-220F
LG-formed



Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FDPF33N25T FDPF33N25TRDTU	Unit
V_{DSS}	Drain-Source Voltage		250	V
I_D	Drain Current	- Continuous (T_C = 25°C) - Continuous (T_C = 100°C)	33* 20.4*	A A
I_{DM}	Drain Current	- Pulsed (Note 1)	132*	A
V_{GSS}	Gate-Source voltage		± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		918	mJ
I_{AR}	Avalanche Current (Note 1)		33	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		23.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns
P_D	Power Dissipation	(T_C = 25°C) - Derate Above 25°C	37 0.29	W W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

*Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FDPF33N25T FDPF33N25TRDTU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	3.4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDPF33N25T	FDPF33N25T	TO-220F	Tube	N/A	N/A	50 units
FDPF33N25TRDTU	FDPF33N25T	TO-220F (LG-formed)	Tube	N/A	N/A	50 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA, T_J = 25°C	250	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	--	0.25	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 250 V, V_{GS} = 0 V V_{DS} = 200 V, T_C = 125°C	-- --	-- --	1 10	μA μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 16.5 A	--	0.077	0.094	Ω
g_{FS}	Forward Transconductance	V_{DS} = 40 V, I_D = 16.5 A	--	26.6	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	1640	2135	pF
C_{oss}	Output Capacitance		--	330	430	pF
C_{rss}	Reverse Transfer Capacitance		--	39	59	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 125 V, I_D = 33 A, V_{GS} = 10 V, R_G = 25 Ω (Note 4)	--	35	80	ns
t_r	Turn-On Rise Time		--	230	470	ns
$t_{d(off)}$	Turn-Off Delay Time		--	75	160	ns
t_f	Turn-Off Fall Time		--	120	250	ns
Q_g	Total Gate Charge	V_{DS} = 200 V, I_D = 33 A, V_{GS} = 10 V (Note 4)	--	36.8	48	nC
Q_{gs}	Gate-Source Charge		--	10	--	nC
Q_{gd}	Gate-Drain Charge		--	17	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	33	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	132	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 33 A	--	--	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 33 A, dI_F/dt =100 A/μs	--	220	--	ns
Q_{rr}	Reverse Recovery Charge		--	1.71	--	μC

Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. L = 1.35 mH, I_{AS} = 33 A, V_{DD} = 50 V, R_G = 25 Ω, starting T_J = 25°C.
3. $I_{SD} \leq 33$ A, di/dt ≤ 200 A/μs, $V_{DD} \leq BV_{DSS}$, starting T_J = 25°C.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

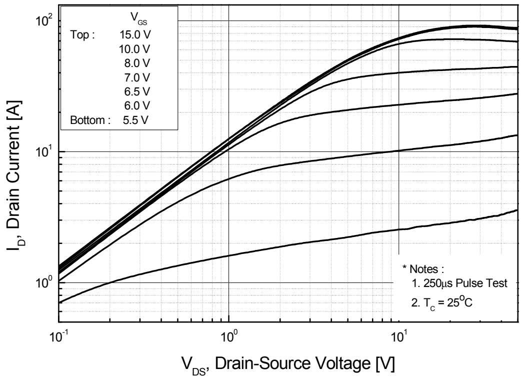


Figure 2. Transfer Characteristics

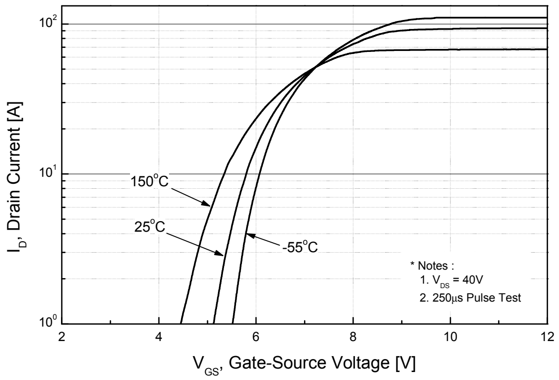


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

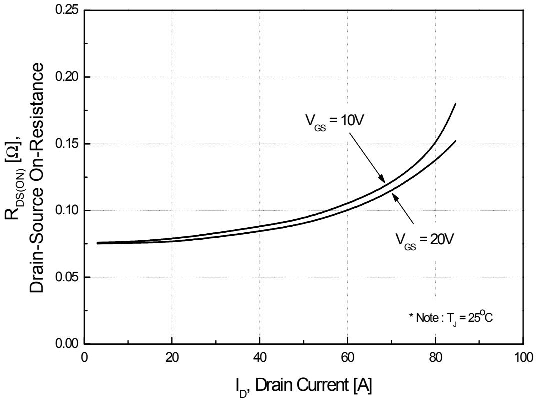


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

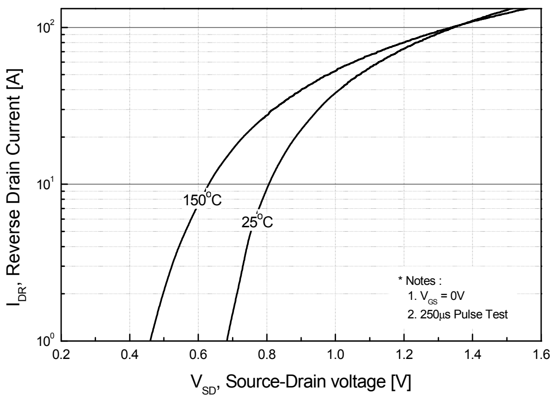


Figure 5. Capacitance Characteristics

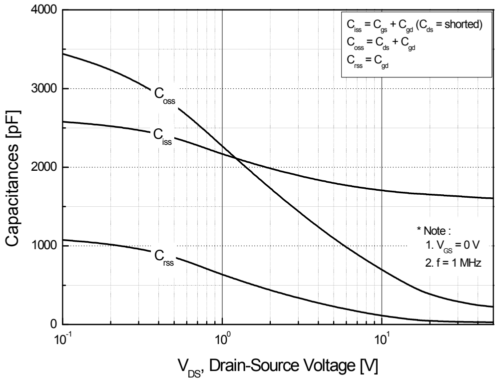
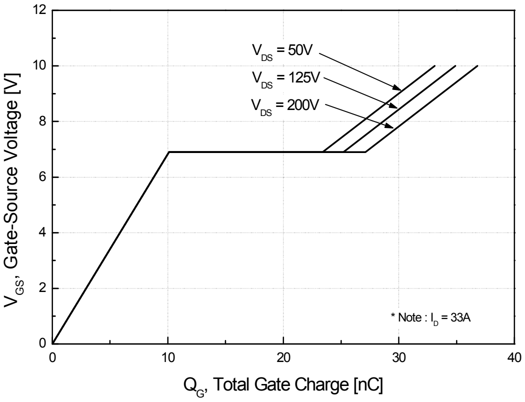


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

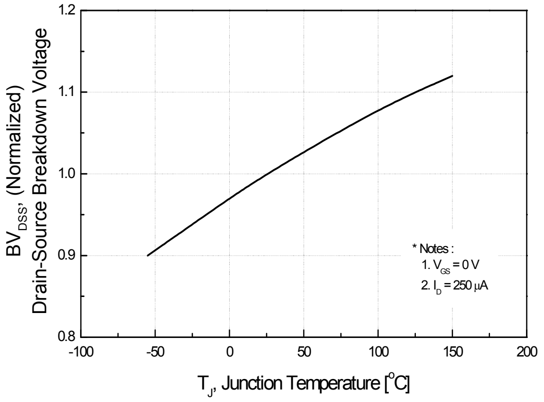


Figure 8. On-Resistance Variation vs. Temperature

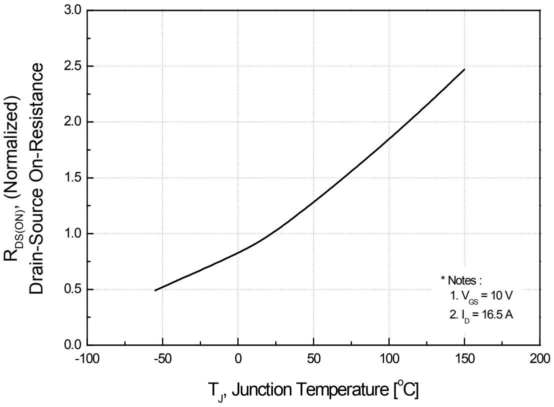


Figure 9. Maximum Safe Operating Area

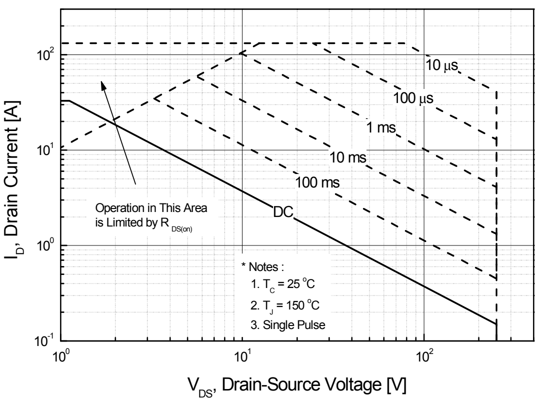


Figure 10. Maximum Drain Current vs. Case Temperature

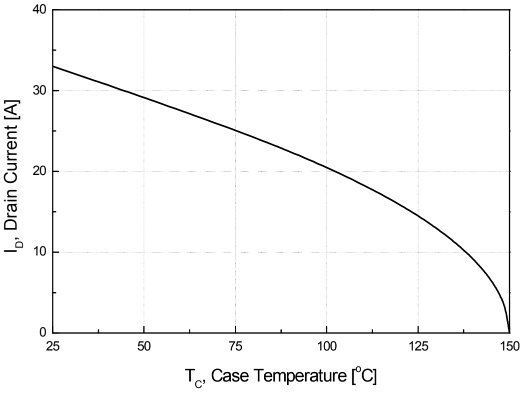
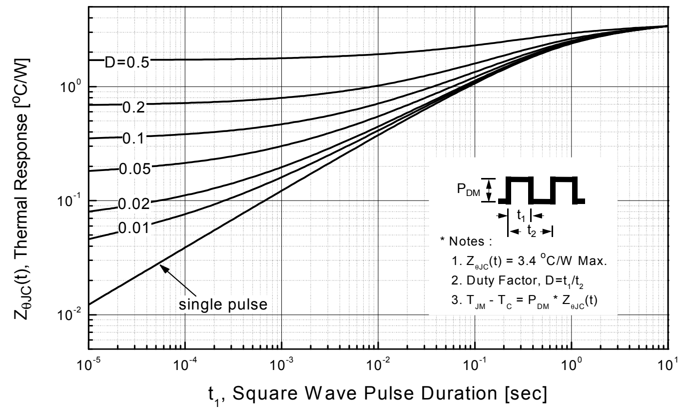


Figure 11. Transient Thermal Response Curve



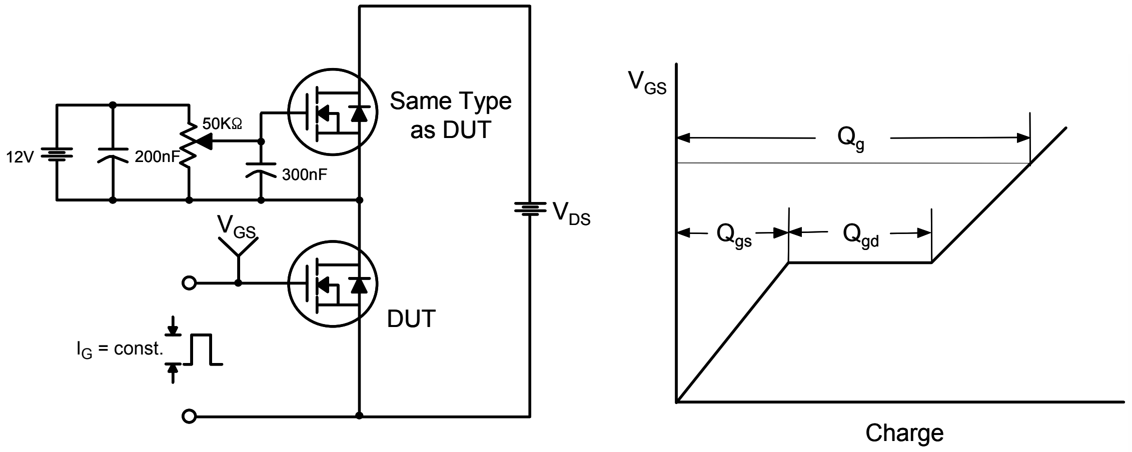


Figure 12. Gate Charge Test Circuit & Waveform

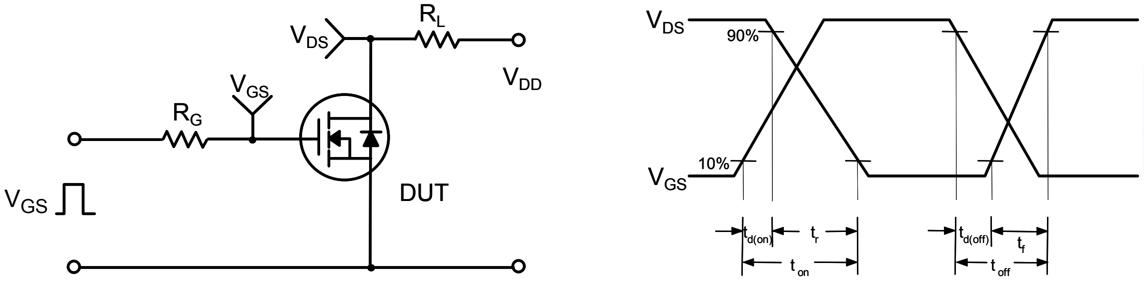
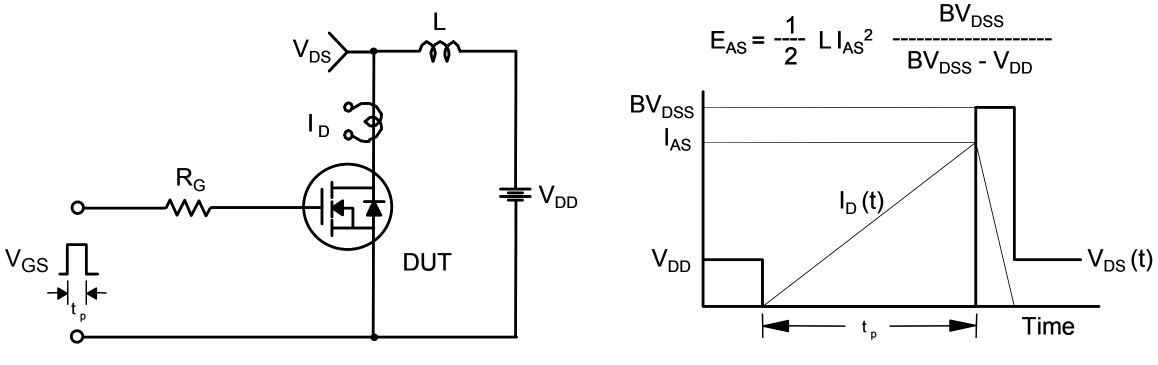


Figure 13. Resistive Switching Test Circuit & Waveforms



$$E_{AS} = \frac{1}{2} L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

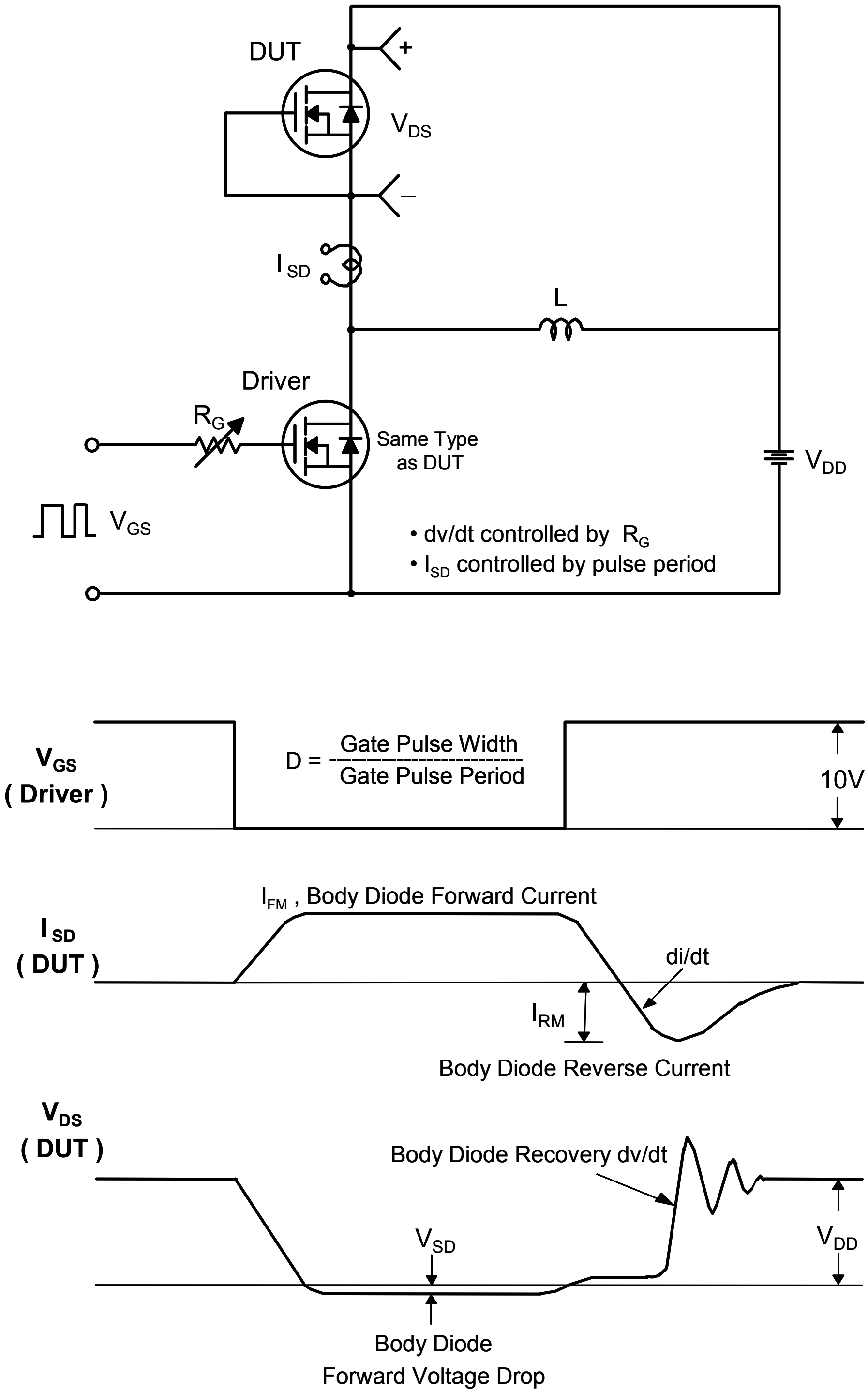
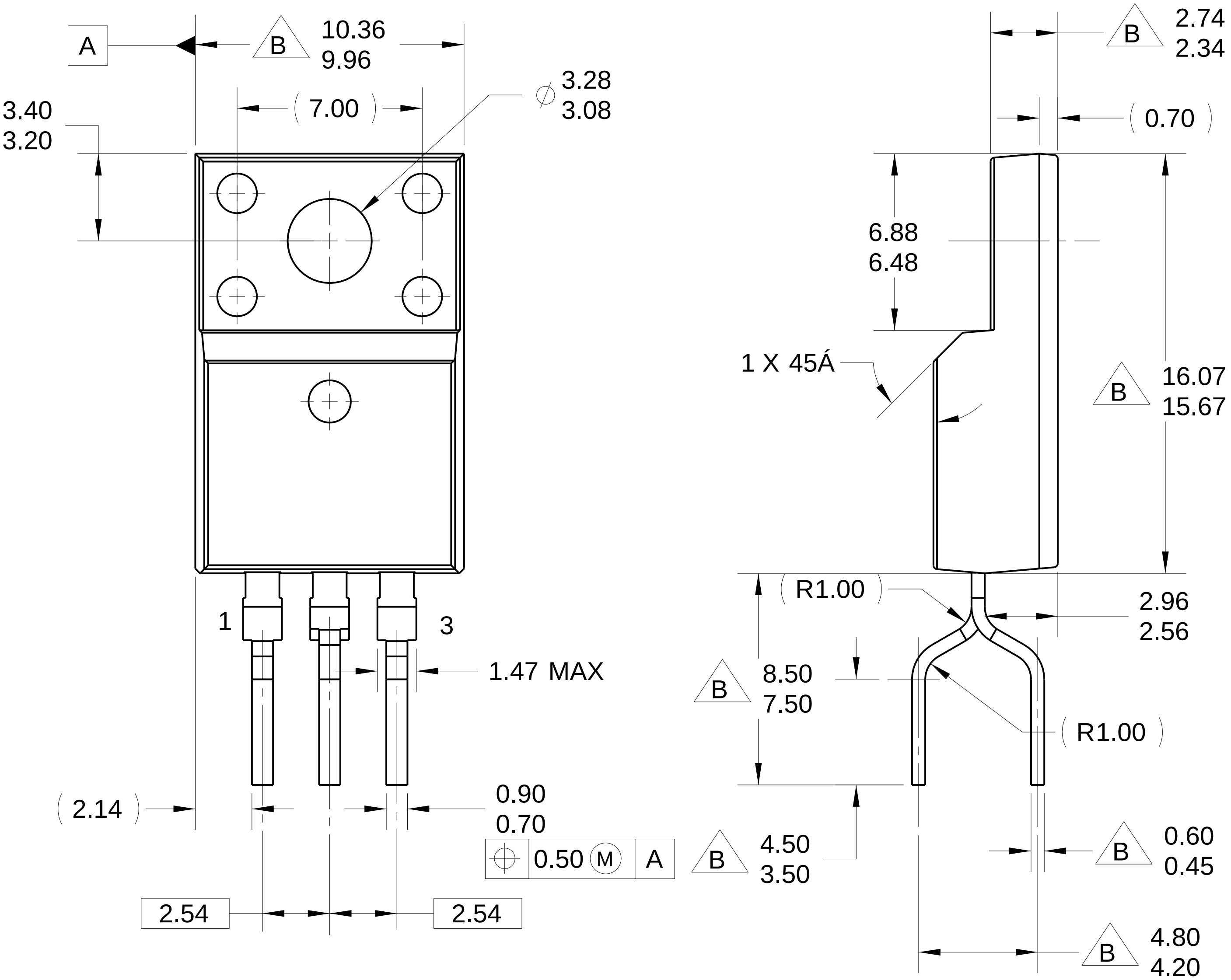
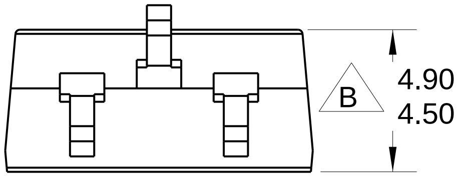


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

REVISIONS

NBR	DESCRIPTION	DATE	BY/APP'D
1	RELEASED TO DCC	04JUN08	SDLEE/ SUZHOU





NOTES:

A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
B. DOES NOT COMPLY EIAJ STD. VALUE.
C. ALL DIMENSIONS ARE IN MILLIMETERS.
D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
F. DRAWING FILE NAME: TO220N03REV1

APPROVALS	DATE
DRAWN: BOBOY MALDO	04JUN08
CHECKED: SD LEE	
APPROVED: BY HUANG	
APPROVED: HOWARD ALLEN	
PROJECTION [MM] INCH	

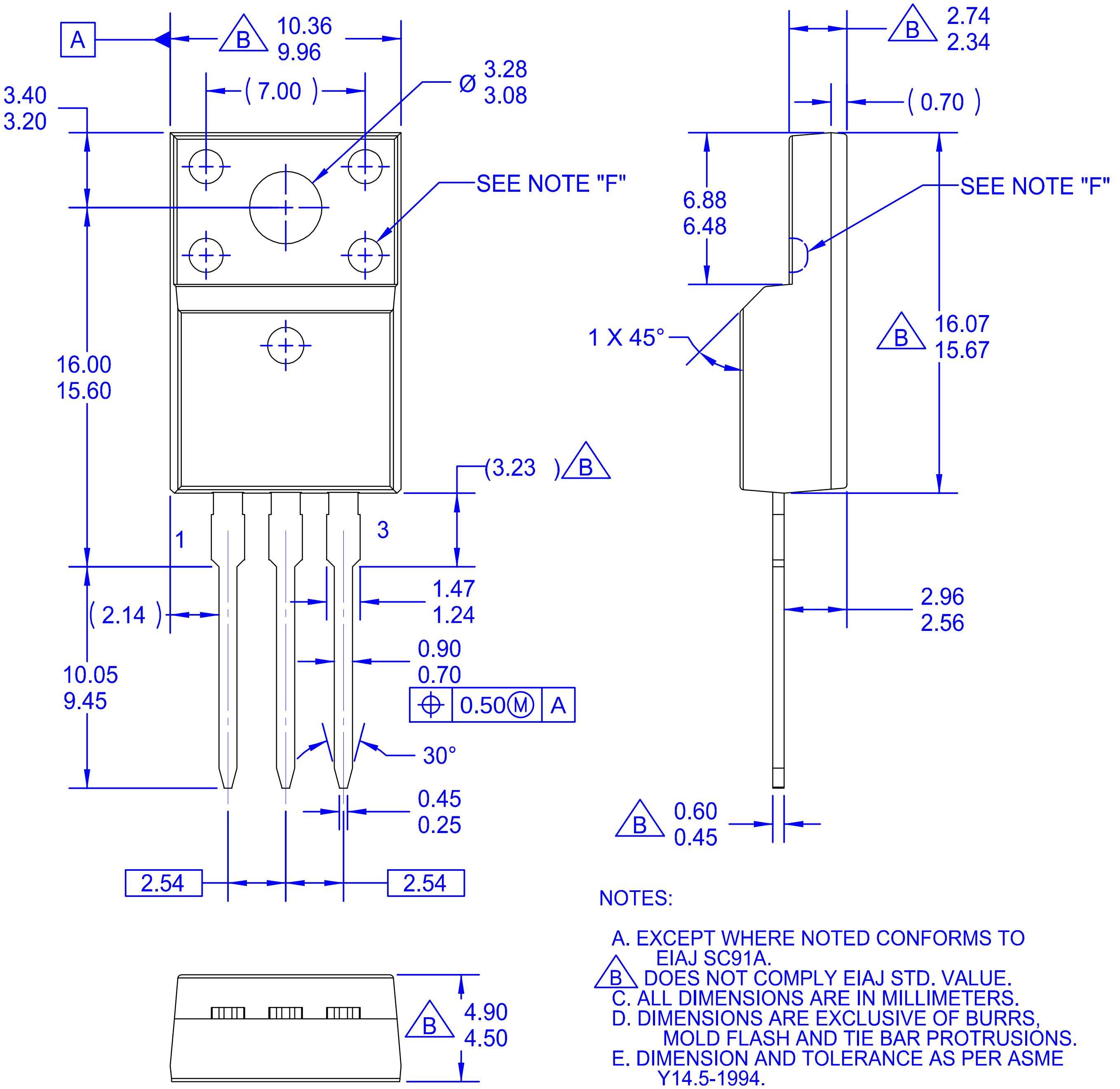
FAIRCHILD SEMICONDUCTOR™

TO220, MOLDED, 3LD, FULL PACK, EIAJ SC91, LG FORM

SCALE	SIZE	DRAWING NUMBER	REV
1:1	N/A	MKT-TO220N03	1

FORMERLY: N/A

SHEET : 1 OF 1



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D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.

E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.

F. OPTION 1 - WITH SUPPORT PIN HOLE.
OPTION 2 - NO SUPPORT PIN HOLE.

G. DRAWING FILE NAME: TO220M03REV4

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No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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Rev. I77